

FEATURES:

- 0.5 MICRON CMOS Technology
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)
- Vcc = 3.3V ± 0.3V, Normal Range
- Vcc = 2.7V to 3.6V, Extended Range
- CMOS power levels (0.4µ W typ. static)
- Rail-to-rail output swing for increased noise margin
- All inputs, outputs, and I/O are 5V tolerant
- Supports hot insertion
- Available in QSOP package

DRIVE FEATURES:

- High Output Drivers: ±24mA
- Reduced system switching noise

APPLICATIONS:

- 5V and 3.3V mixed voltage systems
- Data communication and telecommunication systems

DESCRIPTION:

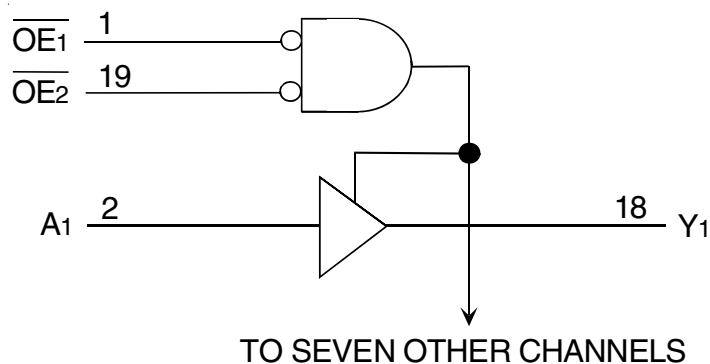
The LVC541A octal buffer/driver is built using advanced dual metal CMOS technology. This device is ideal for driving bus lines or buffer memory address registers. This device features inputs and outputs on opposite sides of the package that facilitate printed circuit board layout. The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all eight outputs are in the high-impedance state.

The LVC541A has been designed with a ±24mA output driver. This driver is capable of driving a moderate to heavy load while maintaining speed performance.

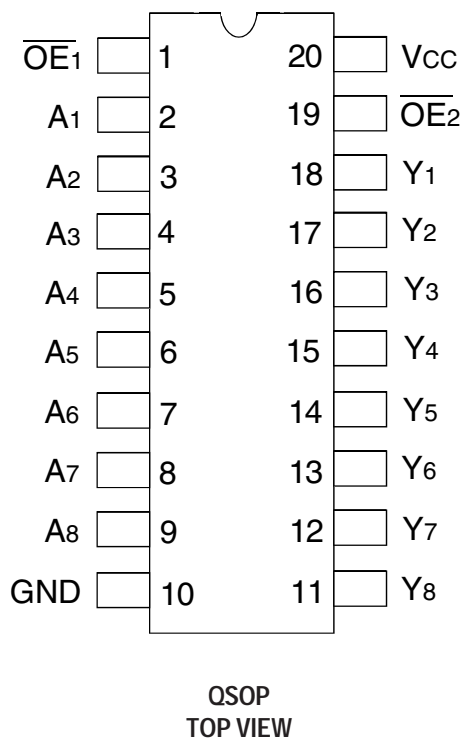
To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to Vcc through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3V or 5V devices. This feature allows the use of this device as a translator in a mixed 3.3V/5V system environment.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +6.5	V
TSTG	Storage Temperature	-65 to +150	°C
I _{OUT}	DC Output Current	-50 to +50	mA
I _{IK} I _{OK}	Continuous Clamp Current, V _I < 0 or V _O < 0	-50	mA
I _{CC} I _{SS}	Continuous Current through each V _{CC} or GND	±100	mA

NOTE:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE (T_A = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	4.5	6	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	5.5	8	pF
C _{I/O}	I/O Port Capacitance	V _{IN} = 0V	6.5	8	pF

NOTE:

- As applicable to the device type.

PIN DESCRIPTION

Pin Names	Description
\overline{OE}_1 , \overline{OE}_2	Output Enable Inputs (Active LOW)
A _x	Data Inputs
Y _x	Data Outputs

FUNCTION TABLE⁽¹⁾

Inputs			Outputs
\overline{OE}_1	\overline{OE}_2	xA _x	xY _x
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

NOTE:

- H = HIGH Voltage Level
X = Don't Care
L = LOW Voltage Level
Z = High-Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Operating Condition: $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$

Symbol	Parameter	Test Conditions		Min.	Typ. ⁽¹⁾	Max.	Unit
V_{IH}	Input HIGH Voltage Level	$V_{CC} = 2.3\text{V}$ to 2.7V		1.7	—	—	V
		$V_{CC} = 2.7\text{V}$ to 3.6V		2	—	—	
V_{IL}	Input LOW Voltage Level	$V_{CC} = 2.3\text{V}$ to 2.7V		—	—	0.7	V
		$V_{CC} = 2.7\text{V}$ to 3.6V		—	—	0.8	
I_{IH} I_{IL}	Input Leakage Current	$V_{CC} = 3.6\text{V}$	$V_I = 0$ to 5.5V	—	—	± 5	μA
I_{OZH} I_{OZL}	High Impedance Output Current (3-State Output pins)	$V_{CC} = 3.6\text{V}$	$V_O = 0$ to 5.5V	—	—	± 10	μA
I_{OFF}	Input/Output Power Off Leakage	$V_{CC} = 0\text{V}$, V_{IN} or $V_O \leq 5.5\text{V}$		—	—	± 50	μA
V_{IK}	Clamp Diode Voltage	$V_{CC} = 2.3\text{V}$, $I_{IN} = -18\text{mA}$		—	-0.7	-1.2	V
V_H	Input Hysteresis	$V_{CC} = 3.3\text{V}$		—	100	—	mV
I_{CCL} I_{CCH} I_{CCZ}	Quiescent Power Supply Current	$V_{CC} = 3.6\text{V}$	$V_{IN} = \text{GND}$ or V_{CC}	—	—	10	μA
			$3.6 \leq V_{IN} \leq 5.5\text{V}^{(2)}$	—	—	10	
ΔI_{CC}	Quiescent Power Supply Current Variation	One input at $V_{CC} - 0.6\text{V}$, other inputs at V_{CC} or GND		—	—	500	μA

NOTES:

1. Typical values are at $V_{CC} = 3.3\text{V}$, $+25^{\circ}\text{C}$ ambient.
2. This applies in the disabled state only.

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	$V_{CC} = 2.3\text{V}$ to 3.6V	$I_{OH} = -0.1\text{mA}$	$V_{CC} - 0.2$	—	V
		$V_{CC} = 2.3\text{V}$	$I_{OH} = -6\text{mA}$	2	—	
		$V_{CC} = 2.3\text{V}$	$I_{OH} = -12\text{mA}$	1.7	—	
		$V_{CC} = 2.7\text{V}$		2.2	—	
		$V_{CC} = 3\text{V}$		2.4	—	
		$V_{CC} = 3\text{V}$	$I_{OH} = -24\text{mA}$	2.2	—	
V_{OL}	Output LOW Voltage	$V_{CC} = 2.3\text{V}$ to 3.6V	$I_{OL} = 0.1\text{mA}$	—	0.2	V
		$V_{CC} = 2.3\text{V}$	$I_{OL} = 6\text{mA}$	—	0.4	
			$I_{OL} = 12\text{mA}$	—	0.7	
		$V_{CC} = 2.7\text{V}$	$I_{OL} = 12\text{mA}$	—	0.4	
		$V_{CC} = 3\text{V}$	$I_{OL} = 24\text{mA}$	—	0.55	

NOTE:

1. V_{IH} and V_{IL} must be within the min. or max. range shown in the DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE table for the appropriate V_{CC} range. $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$.

OPERATING CHARACTERISTICS, $V_{CC} = 3.3V \pm 0.3V$, $T_A = 25^\circ C$

Symbol	Parameter	Test Conditions	Typical	Unit
CPD	Power Dissipation Capacitance per Transceiver Outputs enabled	$C_L = 0pF$, $f = 10MHz$	33	pF
CPD	Power Dissipation Capacitance per Transceiver Outputs disabled		2	

SWITCHING CHARACTERISTICS⁽¹⁾

Symbol	Parameter	$V_{CC} = 2.7V$		$V_{CC} = 3.3V \pm 0.3V$		Unit
		Min.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Ax to Yx	—	5.6	1.5	5.1	ns
t_{PZH} t_{PZL}	Output Enable Time \overline{OE}_x to Yx	—	7.5	1.5	7	ns
t_{PHZ} t_{PLZ}	Output Disable Time \overline{OE}_x to Yx	—	7.7	1.5	7	ns
$t_{SK(o)}$	Output Skew ⁽²⁾	—	—	—	1	ns

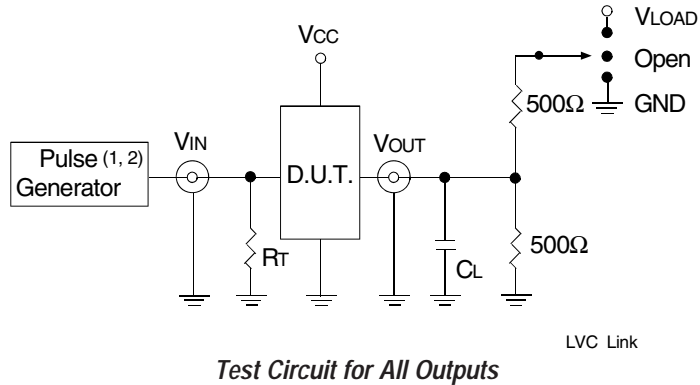
NOTES:

1. See TEST CIRCUITS AND WAVEFORMS. $T_A = -40^\circ C$ to $+85^\circ C$.
2. Skew between any two outputs of the same package and switching in the same direction.

TEST CIRCUITS AND WAVEFORMS

TEST CONDITIONS

Symbol	V _{CC} ⁽¹⁾ = 3.3V ± 0.3V	V _{CC} ⁽¹⁾ = 2.7V	V _{CC} ⁽²⁾ = 2.5V ± 0.2V	Unit
V _{LOAD}	6	6	2 x V _{CC}	V
V _{IH}	2.7	2.7	V _{CC}	V
V _T	1.5	1.5	V _{CC} / 2	V
V _{LZ}	300	300	150	mV
V _{HZ}	300	300	150	mV
C _L	50	50	30	pF



DEFINITIONS:

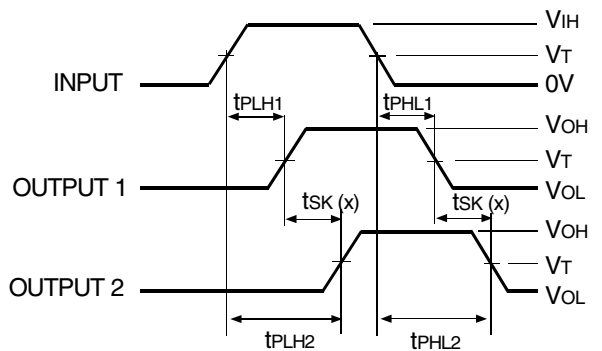
C_L = Load capacitance: includes jig and probe capacitance.
R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

NOTES:

1. Pulse Generator for All Pulses: Rate ≤ 10MHz; t_F ≤ 2.5ns; t_R ≤ 2.5ns.
2. Pulse Generator for All Pulses: Rate ≤ 10MHz; t_F ≤ 2ns; t_R ≤ 2ns.

SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	V _{LOAD}
Disable High Enable High	GND
All Other Tests	Open

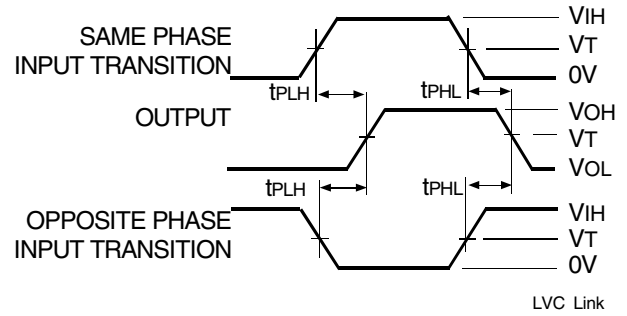


$$tsk(x) = |t_{PLH2} - t_{PLH1}| \text{ or } |t_{PHL2} - t_{PHL1}|$$

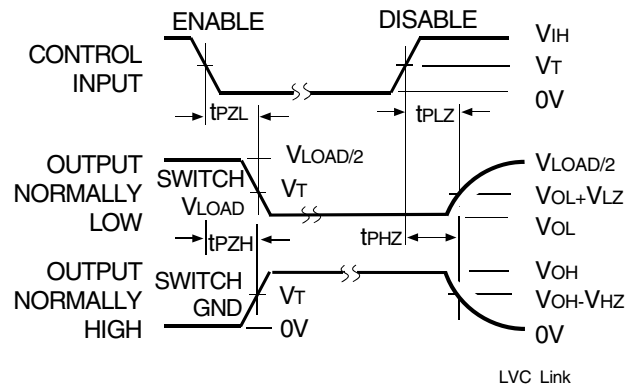
Output Skew - *tsk(x)*

NOTES:

1. For tsk(o) OUTPUT1 and OUTPUT2 are any two outputs.
2. For tsk(b) OUTPUT1 and OUTPUT2 are in the same bank.



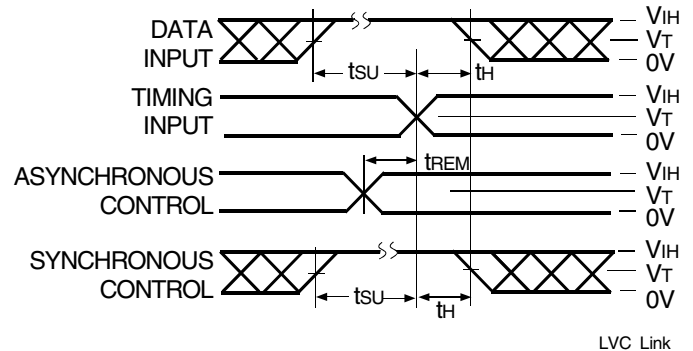
Propagation Delay



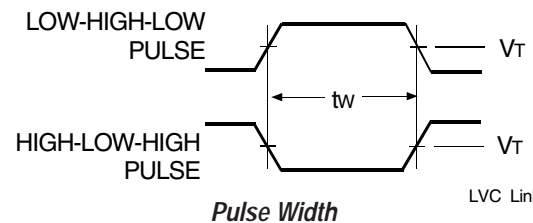
Enable and Disable Times

NOTE:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.

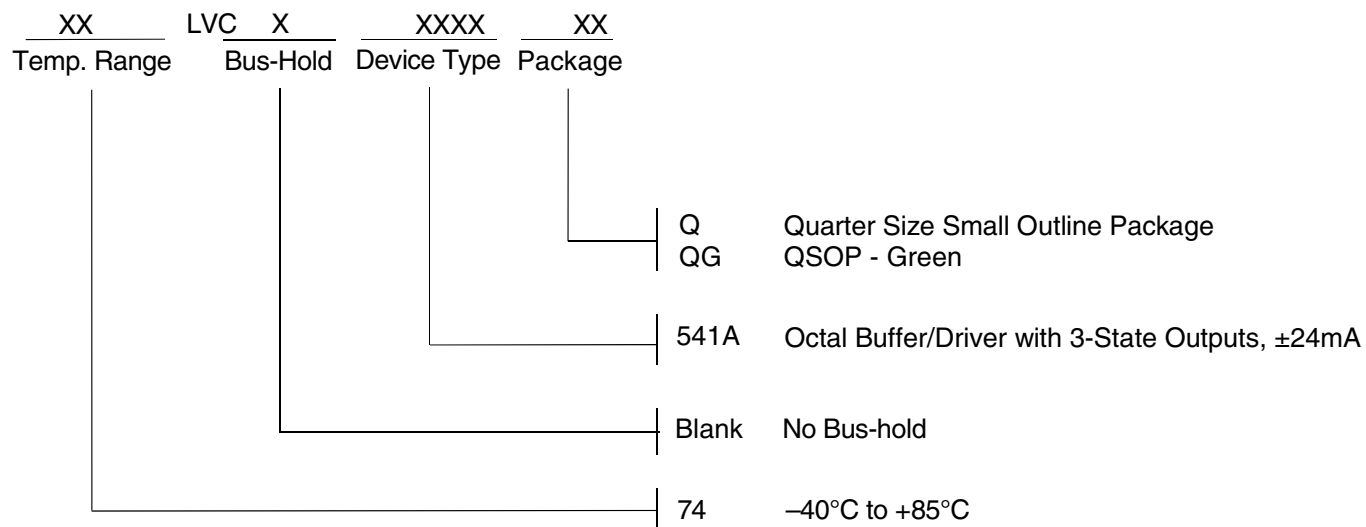


Set-up, Hold, and Release Times



Pulse Width

ORDERING INFORMATION



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